



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	6mΩ @ V _{GS} = 10V	80A
60V	8.5mΩ @ V _{GS} = 4.5V	70A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- · Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

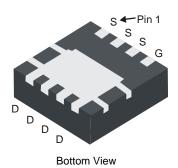
Features and Benefits

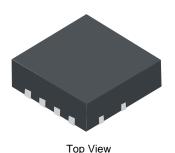
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{gd} × R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area by enabling smaller end products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

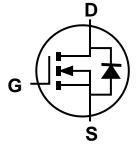
Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

POWERDI®3333-8







Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6007LFG-7	POWERDI®3333-8	2,000/Tape & Reel
DMT6007LFG-13	POWERDI [®] 3333-8	3,000/Tape & Reel

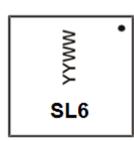
Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information

POWERDI®3333-8



SL6 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 14 = 2014) WW = Week Code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Pusin Courset (Note 5) // 40 //	$T_A = +25$ °C $T_A = +70$ °C	I _D	15 12	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	I _D	80 65	А
Maximum Continuous Body Diode Forward Current (Note 6	I _S	80	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	80	Α	
Avalanche Current, L=0.1mH	I _{AS}	20	А	
Avalanche Energy, L=0.1mH	E _{AS}	20	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	55	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_D	62.5	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	2	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Notes:

^{5.} R_{BJA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.

^{6.} Short duration pulse test used to minimize self-heating effect.

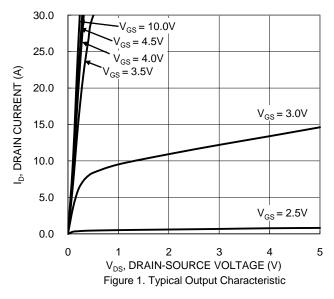


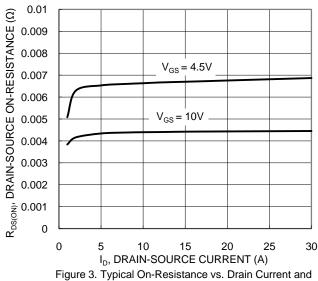
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

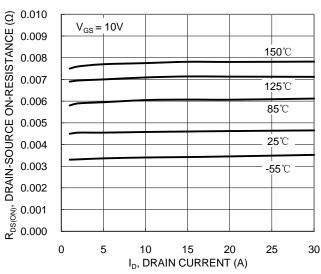
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	0.8	_	2	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	4.5	6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	6.5	8.5	11122	$V_{GS} = 4.5V, I_D = 15A$	
Forward Transconductance	G _{FS}	_	100	_	S	$V_{DS} = 5V, I_{D} = 20A$	
Diode Forward Voltage	V _{SD}	_	0.9	1.2	V	V _{GS} = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	2090	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	746	_	pF		
Reverse Transfer Capacitance	Crss	_	38.5	_			
Gate Resistance	Rq	_	0.59	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	19.3	_		V _{DS} = 30V, I _D = 20A	
Total Gate Charge (V _{GS} = 10V)	Qq	_	41.3	_			
Gate-Source Charge	Qgs	_	6.0	_	nC		
Gate-Drain Charge	Q _{gd}	_	8.8	_			
Turn-On Delay Time	t _{D(ON)}	_	5.7	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 3\Omega$	
Turn-On Rise Time	t _R	_	4.3	_			
Turn-Off Delay Time	t _{D(OFF)}	_	23.4	_	ns		
Turn-Off Fall Time	t _F	_	9.7	_			
Body Diode Reverse Recovery Time	t _{RR}	_	35.4	_	ns	1 000 11/11 4000/	
Body Diode Reverse Recovery Charge	Q_{RR}	_	38.2	_	nC	I _F = 20A, di/dt = 100A/μs	

Note: 7. Guaranteed by design. Not subject to product testing.



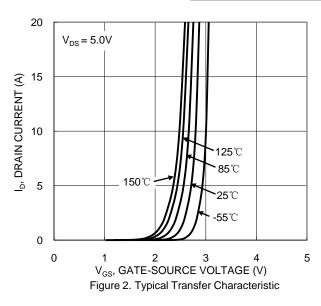


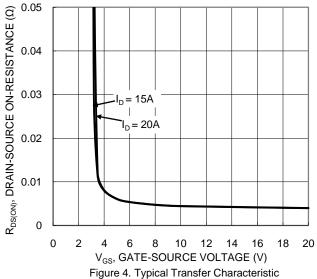




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature





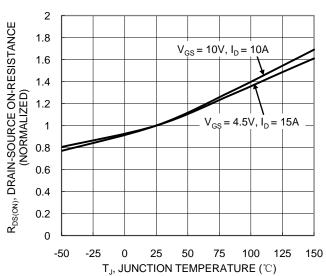
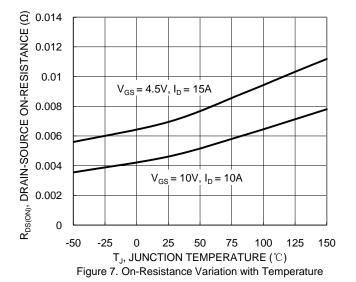


Figure 6. On-Resistance Variation with Temperature





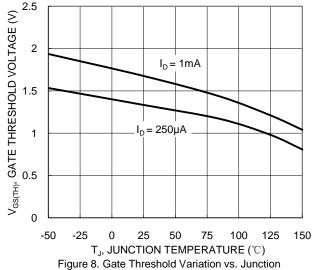
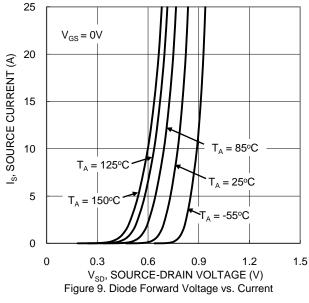
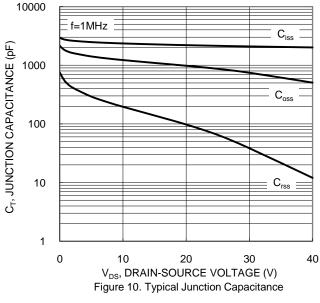
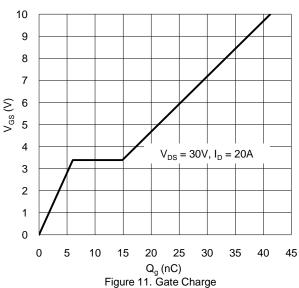
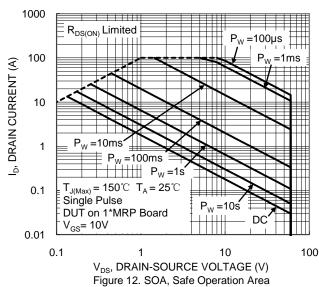


Figure 8. Gate Threshold Variation vs. Junction Temperature











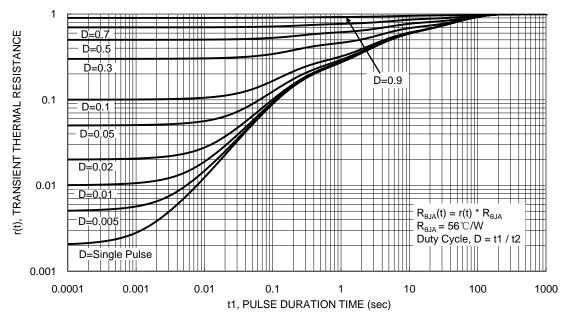


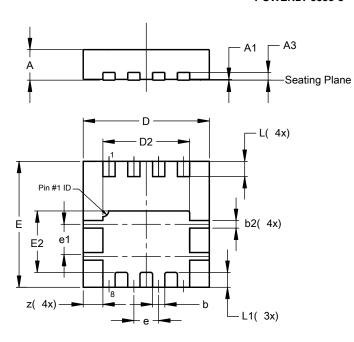
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI®3333-8

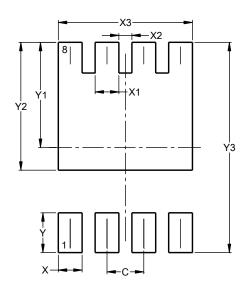


POWERDI®3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	-	-	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All I	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI®3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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